

# J111, J112

## JFET Chopper Transistors

### N-Channel — Depletion

#### Features

- Pb-Free Packages are Available\*

#### MAXIMUM RATINGS

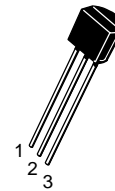
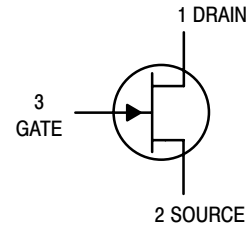
Rating	Symbol	Value	Unit
Drain-Gate Voltage	$V_{DG}$	-35	Vdc
Gate-Source Voltage	$V_{GS}$	-35	Vdc
Gate Current	$I_G$	50	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above = $25^\circ\text{C}$	$P_D$	350 2.8	mW mW/ $^\circ\text{C}$
Lead Temperature	$T_L$	300	$^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



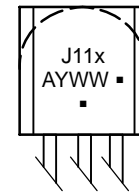
ON Semiconductor®

<http://onsemi.com>



TO-92  
CASE 29-11  
STYLE 5

#### MARKING DIAGRAM



J11x = Device Code  
x = 1 or 2

A = Assembly Location

Y = Year

WW = Work Week

▪ = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# J111, J112

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Gate–Source Breakdown Voltage (I <sub>G</sub> = –1.0 μA <sub>dc</sub> )	V <sub>(BR)GSS</sub>	35	–	V <sub>dc</sub>
Gate Reverse Current (V <sub>GS</sub> = –15 V <sub>dc</sub> )	I <sub>GSS</sub>	–	–1.0	nA <sub>dc</sub>
Gate Source Cutoff Voltage (V <sub>DS</sub> = 5.0 V <sub>dc</sub> , I <sub>D</sub> = 1.0 μA <sub>dc</sub> )	V <sub>GS(off)</sub>	–3.0 –1.0	–10 –5.0	V <sub>dc</sub>
Drain–Cutoff Current (V <sub>DS</sub> = 5.0 V <sub>dc</sub> , V <sub>GS</sub> = –10 V <sub>dc</sub> )	I <sub>D(off)</sub>	–	1.0	nA <sub>dc</sub>
<b>ON CHARACTERISTICS</b>				
Zero–Gate–Voltage Drain Current <sup>(1)</sup> (V <sub>DS</sub> = 15 V <sub>dc</sub> )	I <sub>DSS</sub>	20 5.0 2.0	– – –	mA <sub>dc</sub>
Static Drain–Source On Resistance (V <sub>DS</sub> = 0.1 V <sub>dc</sub> )	r <sub>DS(on)</sub>	– –	30 50	Ω
Drain Gate and Source Gate On–Capacitance (V <sub>DS</sub> = V <sub>GS</sub> = 0, f = 1.0 MHz)	C <sub>dg(on)</sub> + C <sub>sg(on)</sub>	–	28	pF
Drain Gate Off–Capacitance (V <sub>GS</sub> = –10 V <sub>dc</sub> , f = 1.0 MHz)	C <sub>dg(off)</sub>	–	5.0	pF
Source Gate Off–Capacitance (V <sub>GS</sub> = –10 V <sub>dc</sub> , f = 1.0 MHz)	C <sub>sg(off)</sub>	–	5.0	pF

1. Pulse Width = 300 μs, Duty Cycle = 3.0%.

## ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
J111RL1	TO–92	2000 Units / Tape & Reel
J111RL1G	TO–92 (Pb–Free)	
J111RLRA	TO–92	2000 Units / Tape & Reel
J111RLRAG	TO–92 (Pb–Free)	
J111RLRP	TO–92	2000 Units / Tape & Reel
J111RLRPG	TO–92 (Pb–Free)	
J112	TO–92	1000 Units / Bulk
J112G	TO–92 (Pb–Free)	
J112RL1	TO–92	2000 Units / Tape & Reel
J112RL1G	TO–92 (Pb–Free)	
J112RLRA	TO–92	2000 Units / Tape & Reel
J112RLRAG	TO–92 (Pb–Free)	

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL SWITCHING CHARACTERISTICS

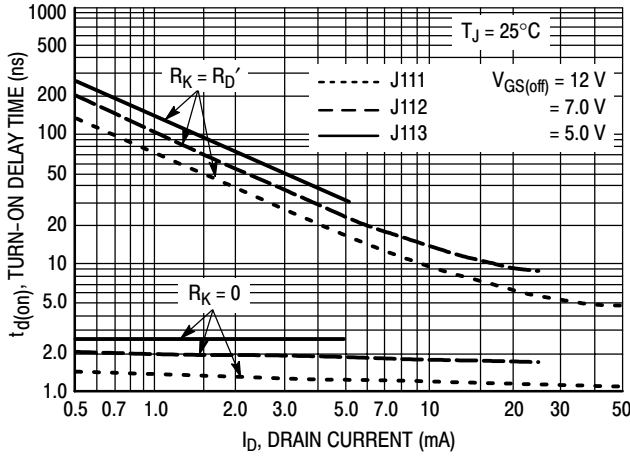


Figure 1. Turn-On Delay Time

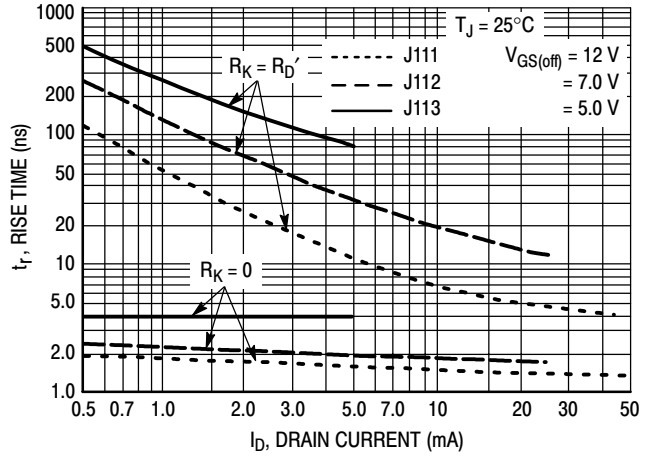


Figure 2. Rise Time

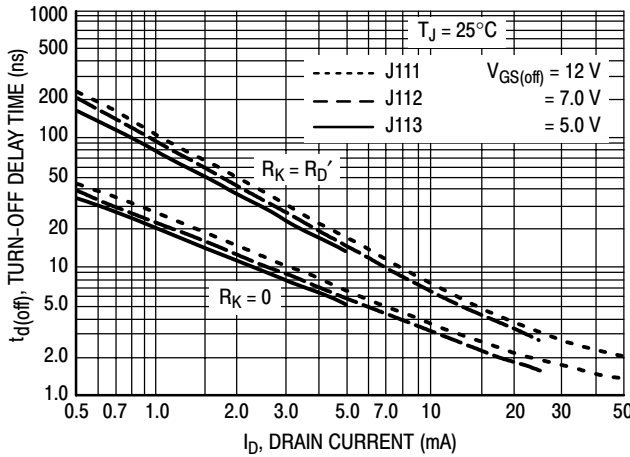


Figure 3. Turn-Off Delay Time

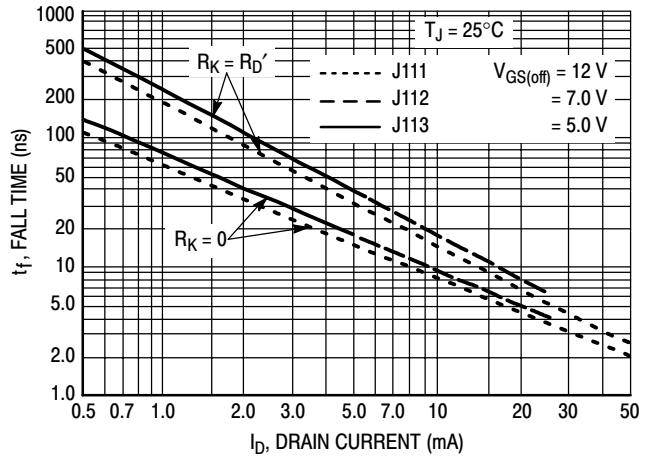


Figure 4. Fall Time

NOTE 1

The switching characteristics shown above were measured using a test circuit similar to Figure 5. At the beginning of the switching interval, the gate voltage is at Gate Supply Voltage ( $-V_{GG}$ ). The Drain-Source Voltage ( $V_{DS}$ ) is slightly lower than Drain Supply Voltage ( $V_{DD}$ ) due to the voltage divider. Thus Reverse Transfer Capacitance ( $C_{rss}$ ) or Gate-Drain Capacitance ( $C_{gd}$ ) is charged to  $V_{GG} + V_{DS}$ .

During the turn-on interval, Gate-Source Capacitance ( $C_{gs}$ ) discharges through the series combination of  $R_{GEN}$  and  $R_K$ .  $C_{gd}$  must discharge to  $V_{DS(on)}$  through  $R_G$  and  $R_K$  in series with the parallel combination of effective load impedance ( $R'_D$ ) and Drain-Source Resistance ( $r_{ds}$ ). During the turn-off, this charge flow is reversed.

Predicting turn-on time is somewhat difficult as the channel resistance  $r_{ds}$  is a function of the gate-source voltage. While  $C_{gs}$  discharges,  $V_{GS}$  approaches zero and  $r_{ds}$  decreases. Since  $C_{gd}$  discharges through  $r_{ds}$ , turn-on time is non-linear. During turn-off, the situation is reversed with  $r_{ds}$  increasing as  $C_{gd}$  charges.

The above switching curves show two impedance conditions; 1)  $R_K$  is equal to  $R_D$ , which simulates the switching behavior of cascaded stages where the driving source impedance is normally the load impedance of the previous stage, and 2)  $R_K = 0$  (low impedance) the driving source impedance is that of the generator.

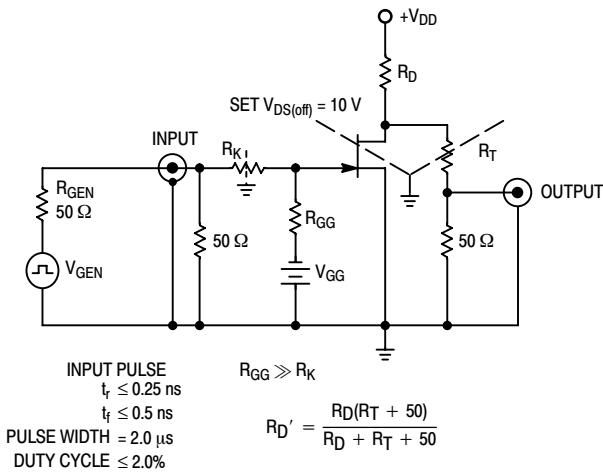


Figure 5. Switching Time Test Circuit

# J111, J112

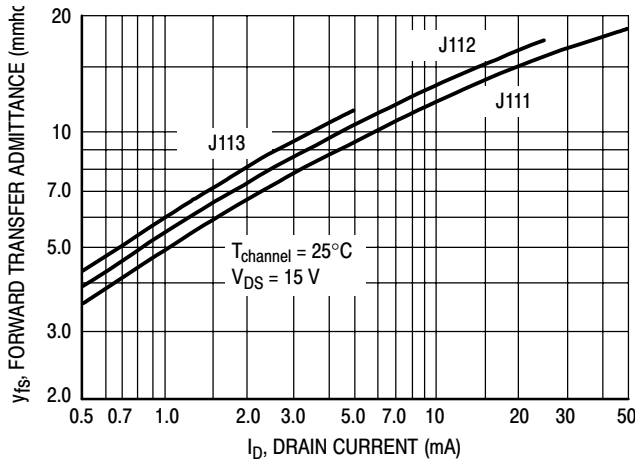


Figure 6. Typical Forward Transfer Admittance

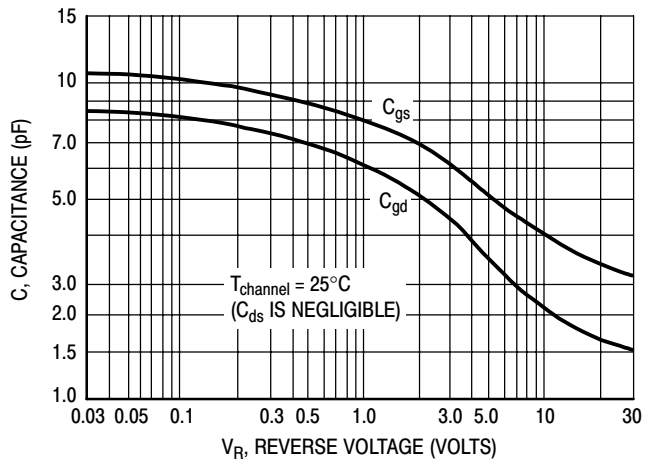


Figure 7. Typical Capacitance

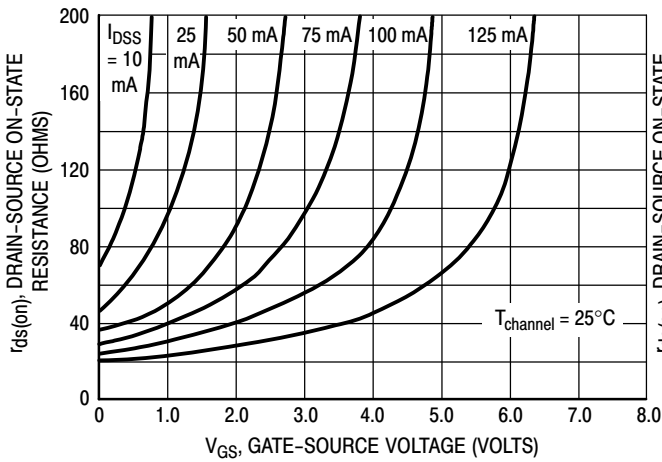


Figure 8. Effect of Gate-Source Voltage On Drain-Source Resistance

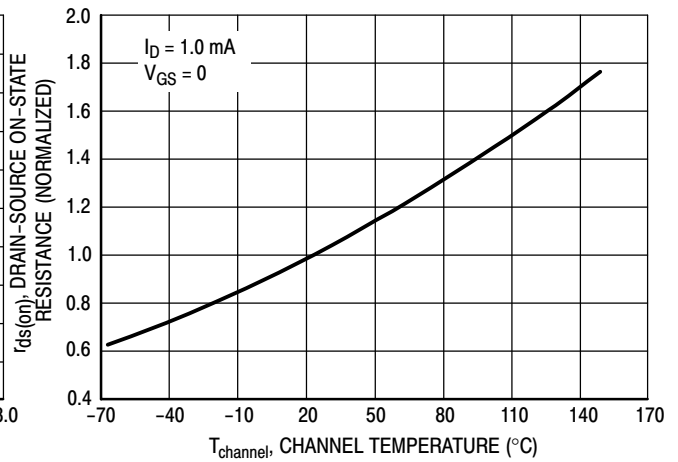


Figure 9. Effect of Temperature On Drain-Source On-State Resistance

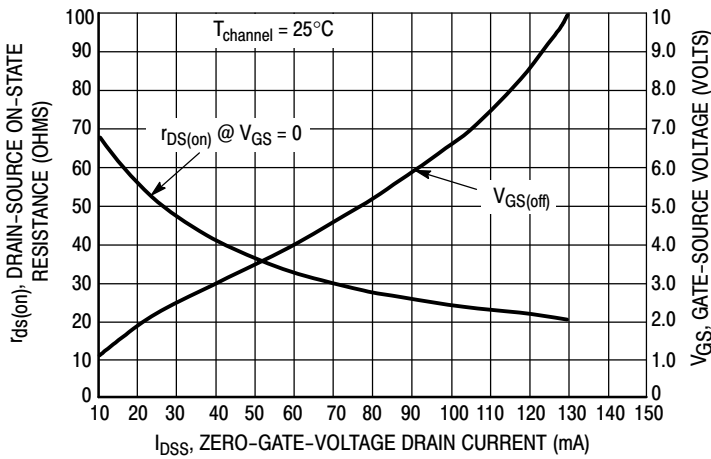


Figure 10. Effect of  $I_{DSS}$  On Drain-Source Resistance and Gate-Source Voltage

## NOTE 2

The Zero-Gate-Voltage Drain Current ( $I_{DSS}$ ), is the principle determinant of other J-FET characteristics. Figure 10 shows the relationship of Gate-Source Off Voltage ( $V_{GS(off)}$ ) and Drain-Source On Resistance ( $r_{ds(on)}$ ) to  $I_{DSS}$ . Most of the devices will be within  $\pm 10\%$  of the values shown in Figure 10. This data will be useful in predicting the characteristic variations for a given part number.

For example:

Unknown

$r_{ds(on)}$  and  $V_{GS}$  range for an J112

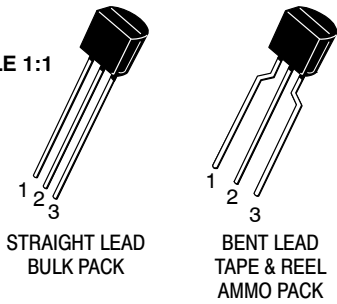
The electrical characteristics table indicates that an J112 has an  $I_{DSS}$  range of 25 to 75 mA. Figure 10, shows  $r_{ds(on)} = 52 \Omega$  for  $I_{DSS} = 25$  mA and  $30 \Omega$  for  $I_{DSS} = 75$  mA. The corresponding  $V_{GS}$  values are 2.2 V and 4.8 V.

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

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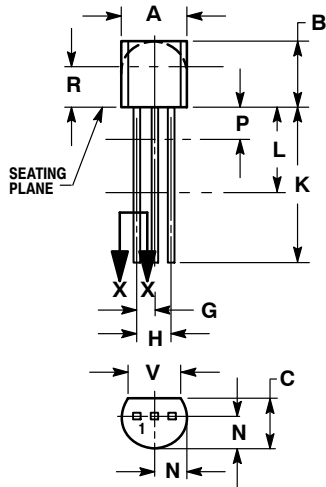


SCALE 1:1



TO-92 (TO-226)  
CASE 29-11  
ISSUE AM

DATE 09 MAR 2007



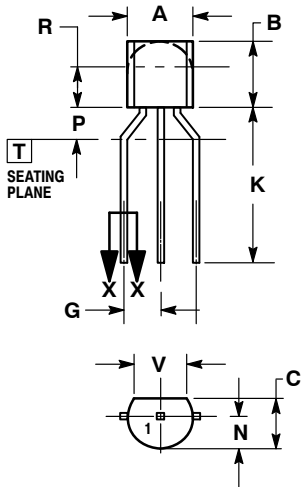
STRAIGHT LEAD  
BULK PACK



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---



BENT LEAD  
TAPE & REEL  
AMMO PACK



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	MILLIMETERS	
	MIN	MAX
A	4.45	5.20
B	4.32	5.33
C	3.18	4.19
D	0.40	0.54
G	2.40	2.80
J	0.39	0.50
K	12.70	---
N	2.04	2.66
P	1.50	4.00
R	2.93	---
V	3.43	---

STYLES ON PAGE 2

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**TO-92 (TO-226)**  
**CASE 29-11**  
**ISSUE AM**

DATE 09 MAR 2007

STYLE 1:  
 PIN 1. EMITTER  
 2. BASE  
 3. COLLECTOR

STYLE 2:  
 PIN 1. BASE  
 2. EMITTER  
 3. COLLECTOR

STYLE 3:  
 PIN 1. ANODE  
 2. ANODE  
 3. CATHODE

STYLE 4:  
 PIN 1. CATHODE  
 2. CATHODE  
 3. ANODE

STYLE 5:  
 PIN 1. DRAIN  
 2. SOURCE  
 3. GATE

STYLE 6:  
 PIN 1. GATE  
 2. SOURCE & SUBSTRATE  
 3. DRAIN

STYLE 7:  
 PIN 1. SOURCE  
 2. DRAIN  
 3. GATE

STYLE 8:  
 PIN 1. DRAIN  
 2. GATE  
 3. SOURCE & SUBSTRATE

STYLE 9:  
 PIN 1. BASE 1  
 2. EMITTER  
 3. BASE 2

STYLE 10:  
 PIN 1. CATHODE  
 2. GATE  
 3. ANODE

STYLE 11:  
 PIN 1. ANODE  
 2. CATHODE & ANODE  
 3. CATHODE

STYLE 12:  
 PIN 1. MAIN TERMINAL 1  
 2. GATE  
 3. MAIN TERMINAL 2

STYLE 13:  
 PIN 1. ANODE 1  
 2. GATE  
 3. CATHODE 2

STYLE 14:  
 PIN 1. EMITTER  
 2. COLLECTOR  
 3. BASE

STYLE 15:  
 PIN 1. ANODE 1  
 2. CATHODE  
 3. ANODE 2

STYLE 16:  
 PIN 1. ANODE  
 2. GATE  
 3. CATHODE

STYLE 17:  
 PIN 1. COLLECTOR  
 2. BASE  
 3. EMITTER

STYLE 18:  
 PIN 1. ANODE  
 2. CATHODE  
 3. NOT CONNECTED

STYLE 19:  
 PIN 1. GATE  
 2. ANODE  
 3. CATHODE

STYLE 20:  
 PIN 1. NOT CONNECTED  
 2. CATHODE  
 3. ANODE

STYLE 21:  
 PIN 1. COLLECTOR  
 2. EMITTER  
 3. BASE

STYLE 22:  
 PIN 1. SOURCE  
 2. GATE  
 3. DRAIN

STYLE 23:  
 PIN 1. GATE  
 2. SOURCE  
 3. DRAIN

STYLE 24:  
 PIN 1. EMITTER  
 2. COLLECTOR/ANODE  
 3. CATHODE

STYLE 25:  
 PIN 1. MT 1  
 2. GATE  
 3. MT 2

STYLE 26:  
 PIN 1. V<sub>CC</sub>  
 2. GROUND 2  
 3. OUTPUT

STYLE 27:  
 PIN 1. MT  
 2. SUBSTRATE  
 3. MT

STYLE 28:  
 PIN 1. CATHODE  
 2. ANODE  
 3. GATE

STYLE 29:  
 PIN 1. NOT CONNECTED  
 2. ANODE  
 3. CATHODE

STYLE 30:  
 PIN 1. DRAIN  
 2. GATE  
 3. SOURCE

STYLE 31:  
 PIN 1. GATE  
 2. DRAIN  
 3. SOURCE

STYLE 32:  
 PIN 1. BASE  
 2. COLLECTOR  
 3. EMITTER

STYLE 33:  
 PIN 1. RETURN  
 2. INPUT  
 3. OUTPUT

STYLE 34:  
 PIN 1. INPUT  
 2. GROUND  
 3. LOGIC

STYLE 35:  
 PIN 1. GATE  
 2. COLLECTOR  
 3. EMITTER

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